TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

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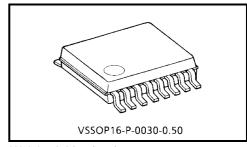
Low Voltage Quad 2-Channel Multiplexer with 3.6 V Tolerant Inputs and Outputs

The TC7MA257FK is a high performance CMOS multiplexer. Designed for use in 1.8 , 2.5 or 3.3 V systems, it achieves high speed operation while maintaining the CMOS low power dissipation.

It is also designed with over voltage tolerant inputs and outputs up to $3.6\ V$.

It consists of four 2-input digital multiplexers with common SELECT and $\overline{OUTPUTENABLE}$ (\overline{OE}).

If \overline{OE} is set high the outputs are held in a high-impedance state. The SELECT decoding determines whether the A or B inputs get routed to their corresponding Y outputs.



Weight: 0.02 g (typ.)

All inputs are equipped with protection circuits against static discharge.

Features

- Low voltage operation: VCC = 1.8~3.6 V
- High speed operation: $t_{pd} = 3.0 \text{ ns (max) (VCC} = 3.0 \sim 3.6 \text{ V)}$

 $t_{pd} = 4.0 \text{ ns (max) (V}_{CC} = 2.3 \sim 2.7 \text{ V})$

 $t_{pd} = 8.0 \text{ ns (max) (VCC} = 1.8 \text{ V)}$

- 3.6 V tolerant inputs and outputs.
- Output current: $I_{OH}/I_{OL} = \pm 24 \text{ mA (min)} (V_{CC} = 3.0 \text{ V})$

 $I_{OH}/I_{OL} = \pm 18 \text{ mA (min) (V}_{CC} = 2.3 \text{ V)}$

 $IOH/IOL = \pm 6 \text{ mA (min) (VCC} = 1.8 \text{ V)}$

- Latch-up performance: ±300 mA
- ESD performance: Machine model > ±200 V

Human body model $> \pm 2000 \text{ V}$

- Package: VSSOP (US16)
- Power down protection is provided on all inputs and outputs.
- Supports live insertion/withdrawal (*)
 - *: To ensure the high-impedance state during power up or power down, $\overline{\text{OE}}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sourcing capability of the driver.

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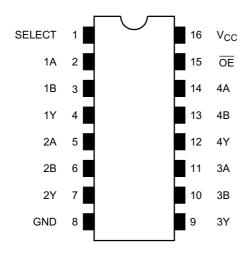
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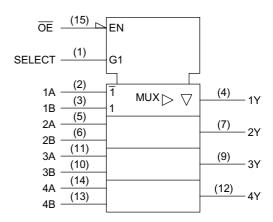
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Pin Assignment (top view)



IEC Logic Symbol



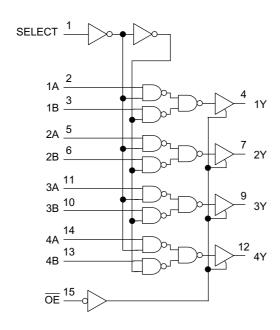
Truth Table

	Outputs			
ŌĒ	SELECT	А	В	Υ
Н	Х	Х	Х	Z
L	L	L	Х	L
L	L	Н	Х	Н
L	Н	X	L	L
L	Н	Х	Н	Н

X: Don't care

Z: High impedance

System Diagram





Maximum Ratings

Characteristics	Symbol	Rating	Unit	
Power supply voltage	V _{CC}	-0.5~4.6	V	
DC input voltage	V _{IN}	-0.5~4.6	V	
		-0.5~4.6 (Note 1)	V	
DC output voltage	Vouт	-0.5~V _{CC} + 0.5 (Note 2)		
Input diode current	I _{IK}	-50	mA	
Output diode current	lok	±50 (Note 3)	mA	
DC output current	lout	±50	mA	
Power dissipation	PD	180	mW	
DC V _{CC} /ground current	I _{CC} /I _{GND}	±100	mA	
Storage temperature	T _{stg}	-65~150	°C	

Note1: Off-state

Note2: High or low state. IOUT absolute maximum rating must be observed.

Note3: $V_{OUT} < GND, V_{OUT} > V_{CC}$

Recommended Operating Range

Characteristics	Symbol	Rating	Unit	
Cumply voltage	V	1.8~3.6	V	
Supply voltage	V _{CC}	1.2~3.6 (Note 4)		
Input voltage	V _{IN}	-0.3~3.6	V	
Output voltage	V	0~3.6 (Note 5)	· V	
Output voltage	V _{OUT}	0~V _{CC} (Note 6)	V	
		±24 (Note 7)		
Output current	I _{OH} /I _{OL}	±18 (Note 8)	mA	
		±6 (Note 9)		
Operating temperature	T _{opr}	-40~85	°C	
Input rise and fall time	dt/dv	0~10 (Note 10)	ns/V	

Note4: Data retention only

Note5: Off-state

Note6: High or low state

Note7: $V_{CC} = 3.0 \sim 3.6 \text{ V}$

Note8: $V_{CC} = 2.3 \sim 2.7 \text{ V}$

Note9: $V_{CC} = 1.8 \text{ V}$

Note10: $V_{IN} = 0.8 \sim 2.0 \text{ V}, V_{CC} = 3.0 \text{ V}$



Electrical Characteristics

DC Characteristics (Ta = -40~85°C, 2.7 V < V_{CC} \leq 3.6 V)

Characte	ristics	Symbol	Test Condition		V _{CC} (V)	Min	Max	Unit
Innut valtage	High level	V_{IH}		_	2.7~3.6	2.0	_	V
Input voltage	Low level	V _{IL}		_	2.7~3.6	_	0.8	٧
				$I_{OH} = -100 \mu A$	2.7~3.6	V _{CC} - 0.2		
	High level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -12 mA	2.7	2.2	_	
				$I_{OH} = -18 \text{ mA}$	3.0	2.4	_	
Output voltage				I _{OH} = -24 mA	3.0	2.2	_	V
-		vel V _{OL}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OL} = 100 \mu A$	2.7~3.6	_	0.2	
	Low level			I _{OL} = 12 mA	2.7	_	0.4	
				$I_{OL} = 18 \text{ mA}$	3.0	_	0.4	
				I _{OL} = 24 mA	3.0	_	0.55	
Input leakage curr	ent	I _{IN}	V _{IN} = 0~3.6 V		2.7~3.6	_	±5.0	μΑ
2 state output off	otata aurrant	1	$V_{IN} = V_{IH}$ or V_{IL}	$V_{IN} = V_{IH}$ or V_{IL}		_	±10.0	_
3-state output off-state current		l _{OZ}	V _{OUT} = 0~3.6 V		2.7~3.6	_	±10.0	μΑ
Power off leakage	current	I _{OFF}	V _{IN} , V _{OUT} = 0~3.6 V		0	_	10.0	μΑ
0.3		loo	$V_{IN} = V_{CC}$ or GND		2.7~3.6	_	20.0	
Quiescent supply	current	Icc	$V_{CC} \le (V_{IN}, V_{OUT}) \le$	' _{CC} ≤ (V _{IN} , V _{OUT}) ≤ 3.6 V		_	±20.0	μΑ
Increase in I _{CC} pe	r input	ΔI_{CC}	$V_{IH} = V_{CC} - 0.6 V$		2.7~3.6	_	750	

DC Characteristics (Ta = -40~85°C, 2.3 V \leq V_{CC} \leq 2.7 V)

Characte	ristics	Symbol	Test Condition		V _{CC} (V)	Min	Max	Unit
land to the sec	High level	V _{IH}		_	2.3~2.7	1.6	_	V
Input voltage	Low level	V _{IL}		_	2.3~2.7	_	0.7	V
				I _{OH} = -100 μA	2.3~2.7	V _{CC} - 0.2	_	
	High level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	$I_{OH} = -6 \text{ mA}$	2.3	2.0	_	
				I _{OH} = -12 mA	2.3	1.8	_	٧
Output voltage				I _{OH} = -18 mA	2.3	1.7	_	
				$I_{OL} = 100 \mu A$	2.3~2.7	_	0.2	
	Low level	V_{OL}	$V_{IN} = V_{IH}$ or V_{IL}	I _{OL} = 12 mA	2.3	_	0.4	
				I _{OL} = 18 mA	2.3	_	0.6	
Input leakage curr	ent	I _{IN}	V _{IN} = 0~3.6 V		2.3~2.7	_	±5.0	μΑ
2 state output off o	otata aummant	1	$V_{IN} = V_{IH}$ or V_{IL}	$V_{IN} = V_{IH}$ or V_{IL}			±10.0	^
3-state output off-state current		l _{OZ}	V _{OUT} = 0~3.6 V		2.3~2.7	_	±10.0	μΑ
Power off leakage	current	l _{OFF}	V _{IN} , V _{OUT} = 0~3.6 V		0	_	10.0	μΑ
		Icc	$V_{IN} = V_{CC}$ or GND	V _{IN} = V _{CC} or GND		_	20.0	^
Quiescent supply	Quiescent supply current		V _{CC} ≤ (V _{IN} , V _{OUT}) ≤ 3.6 V		2.3~2.7	_	±20.0	μА



DC Characteristics (Ta = $-40\sim85^{\circ}$ C, 1.8 V \leq V_{CC} < 2.3 V)

Characteri	Characteristics Symbol Test Condition		Condition	V _{CC} (V)	Min	Max	Unit	
Input voltage	High level	V _{IH}		_	1.8~2.3	0.7 × V _{CC}		V
Input voltage	Low level	V _{IL}		_	1.8~2.3		0.2 × V _{CC}	V
	High level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -100 μA	1.8	V _{CC} - 0.2	I	V
Output voltage				$I_{OH} = -6 \text{ mA}$	1.8	1.4	_	
	Low level	V _{OL}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OL} = 100 \mu A$	1.8	_	0.2	
	LOW level	al AOF		$I_{OL} = 6 \text{ mA}$	1.8		0.3	
Input leakage curre	nt	I _{IN}	V _{IN} = 0~3.6 V		1.8		±5.0	μΑ
3-state output off-state current		I _{OZ}	$V_{IN} = V_{IH}$ or V_{IL} $V_{OUT} = 0 \sim 3.6 \text{ V}$		1.8	_	±10.0	μА
Power off leakage of	urrent	l _{OFF}	V _{IN} , V _{OUT} = 0~3.6 V		0	_	10.0	μА
Quicecent cumply of			V _{IN} = V _{CC} or GND		1.8	_	20.0	^
Quiescent supply cu	urent	Icc	$V_{CC} \le (V_{IN}, V_{OUT}) \le 3.6 \text{ V}$		1.8	_	±20.0	μА

AC Characteristics (Ta = -40~85°C, Input: $t_r = t_f = 2.0$ ns, $C_L = 30$ pF, $R_L = 500$ Ω)

Characteristics	Symbol	Test Condition	V _{CC} (V)	Min	Max	Unit
Propagation delay time	t		1.8	1.0	8.0	
(A, B-Y)	t _{pLH}	Figure 1, Figure 2	2.5 ± 0.2	0.8	4.0	ns
(A, B-1)	t _{pHL}		3.3 ± 0.3	0.6	3.0	
Drangation delay time	4		1.8	1.0	9.6	
Propagation delay time	t _{pLH}	Figure 1, Figure 2	2.5 ± 0.2	0.8	4.8	ns
(SELECT-Y)	t _{pHL}		3.3 ± 0.3	0.6	4.0	
	t _{pZL}	Figure 1, Figure 3	1.8	1.0	9.2	ns
3-state output enable time			2.5 ± 0.2	0.8	4.6	
			3.3 ± 0.3	0.6	3.5	
			1.8	1.0	6.8	
3-state output disable time	t _{pLZ}	Figure 1, Figure 3	2.5 ± 0.2	0.8	3.8	ns
	t _{pHZ}		3.3 ± 0.3	0.6	3.5	
Output to output skew	1		1.8	_	0.5	
	t _{osLH}	(Note 11)	2.5 ± 0.2	_	0.5	ns
	t _{osHL}		3.3 ± 0.3		0.5	

For $C_L = 50~\text{pF}$, add approximately 300 ps to the AC maximum specification.

Note 11: This parameter is guaranteed by design. $(t_{OSLH} = |t_{pLHm} - t_{pLHn}|, \, t_{OSHL} = |t_{pHLm} - t_{pHLn}|)$



Dynamic Switching Characteristics (Ta = 25°C, Input: $t_r = t_f = 2.0$ ns, $C_L = 30$ pF)

Characteristics	Symbol	Test Condition			Тур.	Unit
Characteristics	Symbol			V _{CC} (V)		Offic
		$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (N	Note 12)	1.8	0.25	
Quiet output maximum dynamic V _{OL}	V _{OLP}	$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (N	Note 12)	2.5	0.6	V
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (N	Note 12)	3.3	8.0	
	V _{OLV}	$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (N	Note 12)	1.8	-0.25	V
Quiet output minimum dynamic V _{OL}		$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (N	Note 12)	2.5	-0.6	
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (N	Note 12)	3.3	-0.8	
	V _{OHV}	$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (N	Note 12)	1.8	1.5	
Quiet output minimum dynamic V _{OH}		$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (N	Note 12)	2.5	1.9	V
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (N	Note 12)	3.3	2.2	

Note 12: This parameter is guaranteed by design.

Capacitive Characteristics (Ta = 25°C)

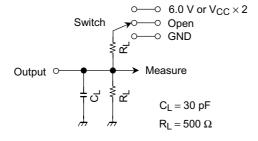
Characteristics	Symbol	Test Condition		Тур.	Unit
Characteristics	Symbol	rest condition	V _{CC} (V)	тур.	
Input capacitance	C _{IN}	_	1.8, 2.5, 3.3	6	pF
Output capacitance	CO	_	1.8, 2.5, 3.3	7	pF
Power dissipation capacitance	C _{PD}	$f_{\text{IN}} = 10 \text{ MHz}$ (Note	13) 1.8, 2.5, 3.3	20	pF

Note 13: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$

AC Test Circuit



Parameter	Switch
t _{pLH} , t _{pHL}	Open
t _{pLZ} , t _{pZL}	$ \begin{array}{cccccccccccccccccccccccccccccccccccc$
t _{pHZ} , t _{pZH}	GND

Figure 1

AC Waveform

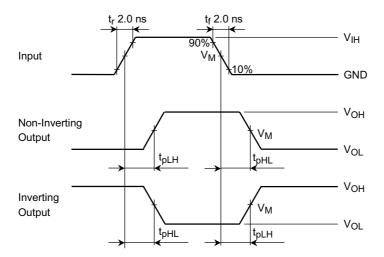


Figure 2 t_{pLH}, t_{pHL}

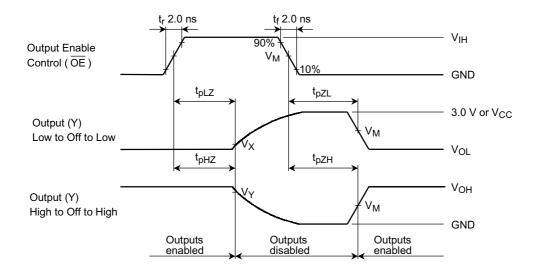
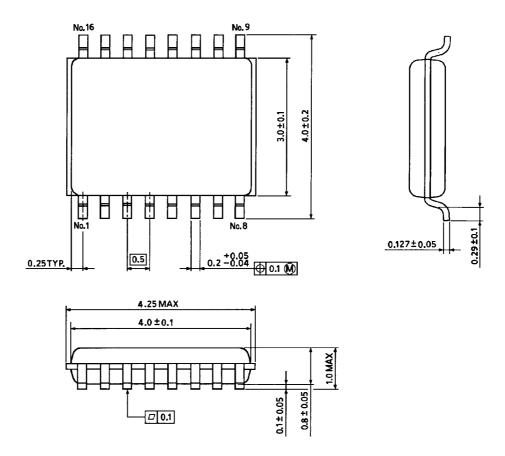


Figure 3 t_{pLZ} , t_{pHZ} , t_{pZL} , t_{pZH}

Symbol		V _{CC}	
Symbol	$3.3\pm0.3~\text{V}$	2.5 ± 0.2 V	1.8 V
V _{IH}	2.7 V	V _{CC}	V _{CC}
V _M	1.5 V	V _{CC} /2	V _{CC} /2
V _X	V _{OL} + 0.3 V	V _{OL} + 0.15 V	V _{OL} + 0.15 V
VY	V _{OH} – 0.3 V	V _{OH} – 0.15 V	V _{OH} – 0.15 V

Package Dimensions



Weight: 0.02 g (typ.)